

**Trans IGBT Chip N-CH 1700V 16A 120mW 3-Pin(3+Tab)  
ISOPLUS 247**



Images are for reference only

[Inquiry](#)

**Manufacturer:** [Littelfuse Inc](#)

**Package/Case:** ISOPLUS247

**Product Type:** Thyristors

**Lifecycle:** Obsolete

## General Description

BiMOSFETs are devices, which have combined strengths of MOSFETs and IGBTs. Non-epitaxial construction and new fabrication processes were used in making BiMOSFETs a great success. These high voltage devices are ideal for parallel operation due to the positive voltage temperature coefficient of both of its saturation voltage, and the forward voltage drop of its intrinsic diode. Furthermore, this “free” intrinsic body diode serves as a protection diode, providing an alternative path for the inductive load current during device turn-off, preventing high  $Ldi/dt$  voltage transients from inflicting damage to the device.

## Key Features

- Silicon chip on direct-copper bond (DCB) substrate
- Isolated mounting surface
- Anti-parallel sonic diode
- High power density
- Low gate drive requirement
- 2500V Electrical isolation

## Application

- Radar transmitter power supplies
- Radar pulse modulators
- Capacitor discharge circuits
- High voltage power supplies
- AC switches
- HV circuit breakers
- Pulser circuits
- High voltage test equipment
- Laser & X-ray generators

## Recommended For You

**IXGH48N60C3D1**

Littelfuse Inc

TO-247

**IXYX100N120C3**

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PLUS247

**IXGH30N60B2D1**

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**IXYN30N170CV1**

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N

**IXBH16N170**

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**IXGH60N60C2**

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**IXGH48N60A3**

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**IXGN320N60A3**

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MODULE

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**IXYR50N120C3D1**

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